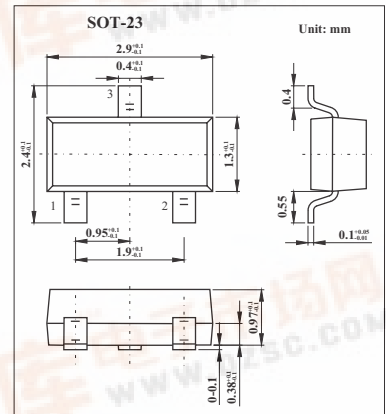


SMD Type Diodes

Silicon PIN Diodes
BAR17

■ Features

- RF switch
- RF attenuator for frequencies above 1 MHz
- Low distortion factor
- Long-term stability of electrical characteristics



■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Value	Unit
Reverse voltage	V _R	100	V
Forward current	I _F	140	mA
Total power dissipation, T _s ≤ 95 °C ¹⁾	P _{tot}	250	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C
Operating temperature range	T _{op}	-55 to +150	°C
Junction - ambient ¹⁾	R _{thJA}	≤ 295	K/W
Junction - soldering point	R _{thJS}	≤ 215	

Note

1. Package mounted on alumina 15 mm × 16.7 mm × 0.7 mm.

■ Electrical Characteristics Ta = 25 °C

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse current	I _R	V _R = 50 V			50	nA
		V _R = 100 V			1	μA
Forward voltage	V _F	I _F = 100 mA		0.91	1	V
Diode capacitance	C _T	V _R = 50 V, f = 1 MHz		0.32	0.55	pF
		V _R = 0, f = 100 MHz		0.37		
Charge carrier life time	τ _L	I _F = 10 mA, I _R = 6 mA		4		μs
Forward resistance	r _f	I _F = 0.01 mA, f = 100 MHz		1150		Ω
		I _F = 0.1 mA, f = 100 MHz		160		
		I _F = 1 mA, f = 100 MHz		23		
		I _F = 10 mA, f = 100 MHz		3.5		

■ Marking

Marking	L6
---------	----

